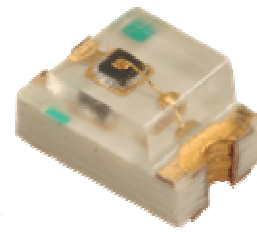


# Infrared Light Emitting Diode in Miniature SMD Package

## OP200

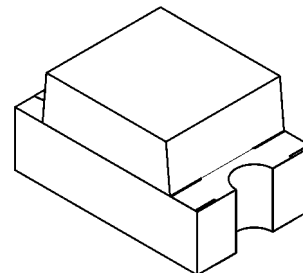
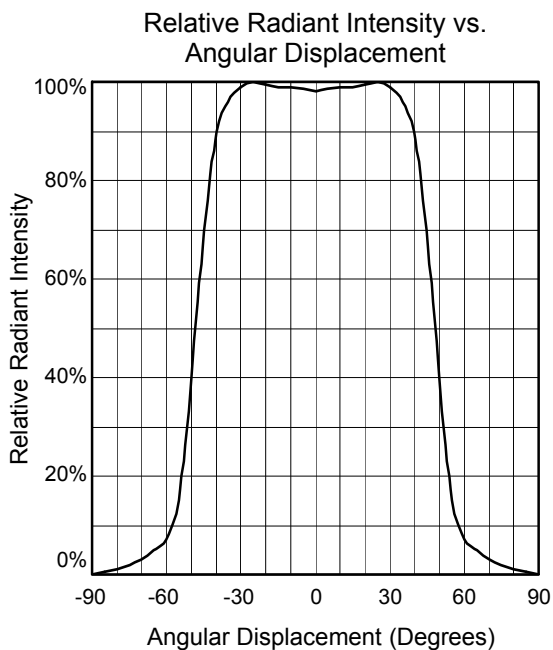
- Flat Lens
- High Power
- 0805 Package Size
- 880nm Wavelength



The OP200 is a GaAlAs infrared LEDs mounted in a miniature SMT package. The device incorporates a flat molded lens which enables a wide beam angle and provides an even emission pattern. This device is packaged in a 0805 size chip carrier that is compatible with most automated mounting equipment. The OP200 is mechanically and spectrally matched to the OP520 series phototransistors.

### Applications

- Non-Contact Position Sensing
- Machine automation
- Datum detection
- Optical encoders



OP200



RoHS

Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  unless otherwise noted

Storage Temperature Range	-40° C to +85° C
Operating Temperature Range	-25° C to +85° C
Lead Soldering Temperature	260° C <sup>(1)</sup>
Reverse Voltage	30 V
Continuous Forward Current	50 mA
Power Dissipation	130 mW <sup>(2)</sup>

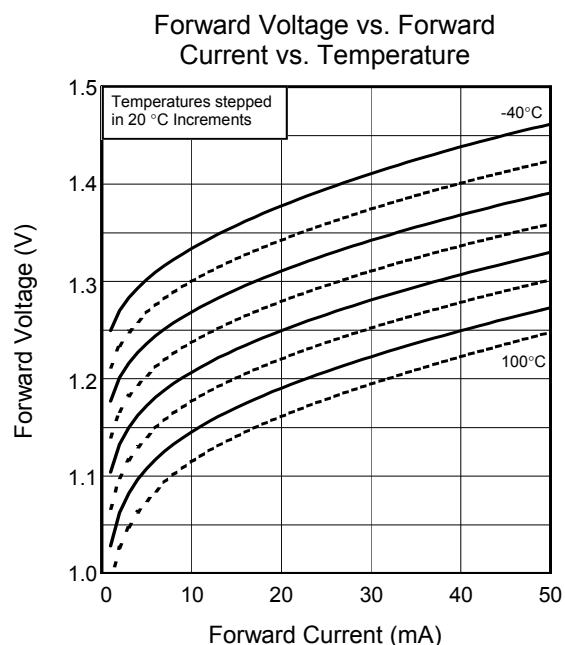
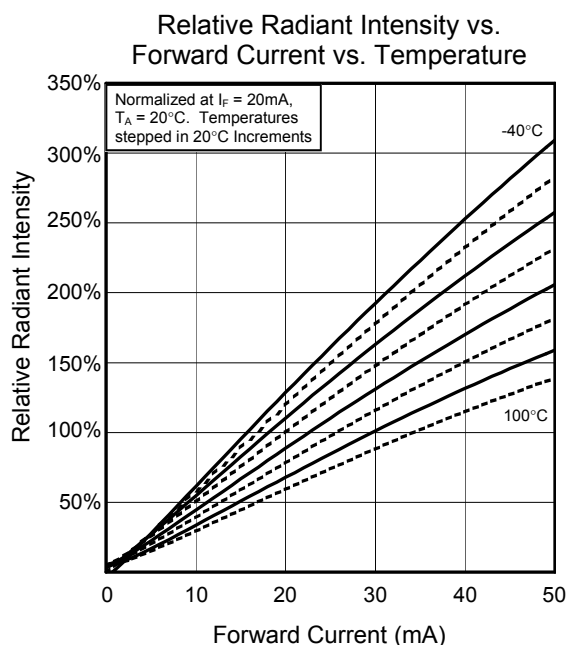
Notes:

- Solder time less than 5 seconds at temperature extreme.
- De-rate linearly at 2.17 mW/° C above 25° C.

### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

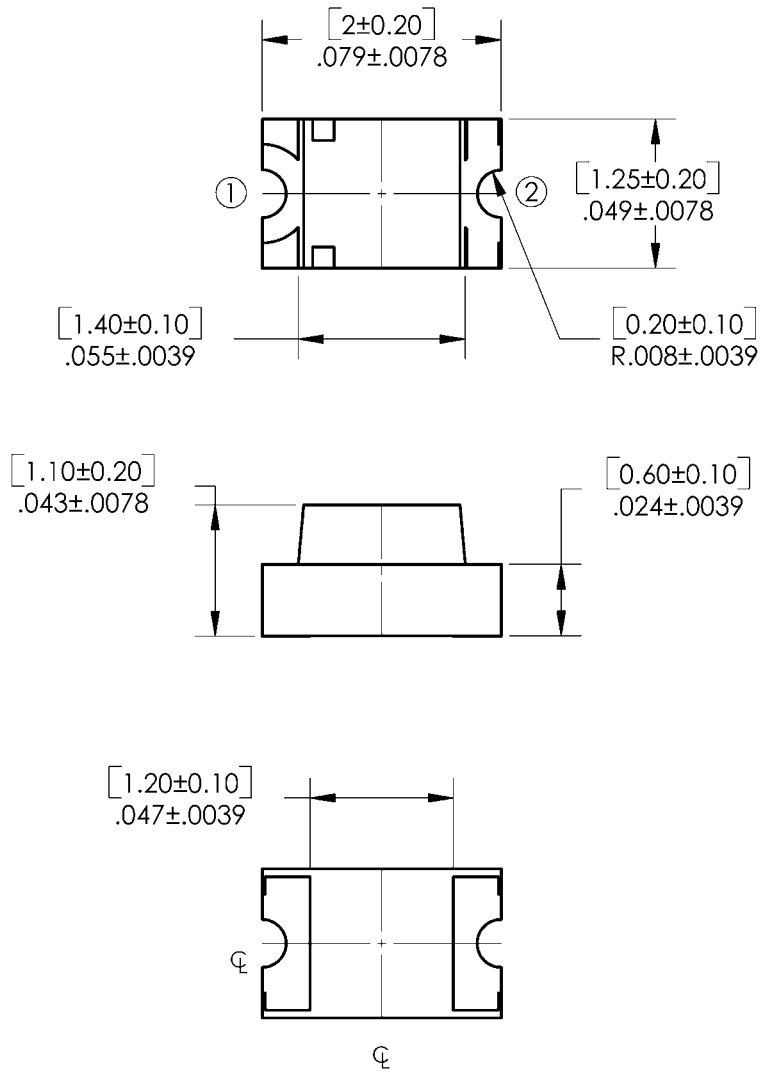
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
$E_{e(\text{APT})}$	Apertured Radiant Incidence	0.2			mW/cm <sup>2</sup>	$I_F = 20\text{mA}^{(3)}$
$V_F$	Forward Voltage			1.5	V	$I_F = 20\text{mA}$
$I_R$	Reverse Current			100	μA	$V_R = 2.0\text{V}$
$\lambda_P$	Peak Emission Wavelength		890		nm	$I_F = 10\text{mA}$
$\Theta_{\text{HP}}$	Emission Angle at Half Power Points		100		Deg.	$I_F = 20\text{mA}$
$t_r, t_f$	Rise and Fall Time			500	ns	$I_{F(\text{PEAK})} = 100\text{mA}$ , PW = 10μs, 10% D.C.

- $E_{e(\text{APT})}$  is a measurement of the apertured radiant incidence upon a sensing area 0.081" (2.06mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99mm) from the measurement surface.  $E_{e(\text{APT})}$  is not necessarily uniform within the measured area.



# SMD Infrared LED

## OP200



PIN	FUNCTION
1	Anode
2	Cathode

DIMENSIONS ARE IN INCHES AND [MILLIMETERS].